L Number	Hits	Search Text	DB	Time stamp
1 Number		(257/645).CCLS.	USPAT;	2002/05/13 17:26
1			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
2	2	((257/645).CCLS.) and trap with (density	USPAT;	2002/05/13 16:45
_		carrier impurity holes electron) same	US-PGPUB;	
		nitride	EPO; JPO;	
			DERWENT;	
			IBM_TDB	2002/05/13 17:02
3	182	(257/\$).ccls. and trap with (density	USPAT; US-PGPUB;	2002/03/13 17:02
		carrier impurity holes electron) same	EPO; JPO;	
		nitride	DERWENT;	
İ			IBM TDB	
		1 1th and twon with (doneity	USPAT;	2002/05/13 17:01
4	154	control with gate and trap with (density	US-PGPUB;	2002,00,10 11101
		carrier impurity holes electron) same	EPO; JPO;	
		nitride	DERWENT;	
			IBM TDB	
_	83	(control with gate and trap with (density	USPAT;	2002/05/13 17:02
5	83	carrier impurity holes electron) same	US-PGPUB;	
		nitride) not ((257/\$).ccls. and trap with	EPO; JPO;	
		(density carrier impurity holes electron)	DERWENT;	
		same nitride)	IBM TDB	
6	3	5907183.pn.	USPAT;	2002/05/13 17:27
0	J	3301103.	US-PGPUB;	[
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
7	3	5731238.pn.	USPAT;	2002/05/13 17:27
			US-PGPUB;	
			EPO; JPO;	!
			DERWENT;	
			IBM_TDB	2002/05/13 10:55
-	18	insulation with layer with trap with	USPAT; US-PGPUB;	2002/03/13 10:33
		density	EPO; JPO;	
			DERWENT;	
			IBM TDB	
	_	sa the sale mate with tran add density	USPAT;	2002/05/11 12:02
-	5	floating adj gate with trap adj density	US-PGPUB;	2002,00,22
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	6	("4154873" "4331709" "4447272"	USPAT	2002/05/10 16:23
-	0	"5010024" "5017979" "5019533").PN.		
1_	135		USPAT;	2002/05/11 12:20
		insulating insulator flating adj gate	US-PGPUB;	
		control adj gate ONO NON) with trap adj	EPO; JPO;	
		density	DERWENT;	
		-	IBM_TDB	
_	26	silicon adj nitride with trap adj density	USPAT;	2002/05/11 14:38
]			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	2002/05/11 14.20
_	8	1 .	USPAT;	2002/05/11 14:38
		same hydrogen	US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
	_	5721222	USPAT;	2002/05/13 11:02
-	3	5731238.pn.	US-PGPUB;	2002,00,10 11.02
			EPO; JPO;	
1			DERWENT;	
1				

		nydrogen with NON with insulating	10020	2002/05/13 11:04
	174	nydrogen with NON with insulating	US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	1
		and a start and	USPAT;	2002/05/13 11:03
	2	(hydrogen with NON with insulating) and	US-PGPUB;	
		floating with gate	EPO; JPO;	1
			DERWENT;	
			IBM_TDB	2002/05/13 11:07
	31	(hydrogen with NON with insulating) and	USPAT; US-PGPUB;	2002/03/13 1211
	31	nitride with hydrogen	EPO; JPO;	
1			DERWENT;	
			IBM TDB	
į		silicon with nitride with hydrogen and	USPAT;	2002/05/13 11:18
-	82	floating with gate	US-PGPUB;	
		floating with gate	EPO; JPO;	
			DERWENT; IBM TDB	
		#505,000EH	USPAT	2002/05/13 11:14
_	7	("4688078" "4788082" "5256205"	002112	
	'	"5356672" "5356673" "5366697"		2002/05/13 11:39
		"5403399").PN.	USPAT;	2002/05/13 11:39
_	3	5483097.pn.	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM_TDB	
			USPAT	2002/05/13 11:18
-	4	5483097.URPN.	USPAT;	2002/05/13 11:43
	1009419	silicon adj nitride wiht density	US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
			USPAT;	2002/05/13 11:40
_	33960	(silicon adj nitride wiht density) and	US-PGPUB;	
		(257/\$).ccls.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	2002/05/13 11:41
	43257	(silicon adj nitride wiht density) and	uspAT; and us-PGPUB;	
-	43237	inter aid layer and floating with gate	EPO; JPO;	
		(257/\$).ccls.	DERWENT;	
	1		IBM TDB	2000/05/12 11:42
		(silicon adj nitride wiht density) and	USPAT;	2002/05/13 11:43
_	95	inter adj layer and floating with gate	and US-PGPUB;	
		(257/\$).ccls.	EPO; JPO; DERWENT;	
		\ \tag{\tag{\tag{\tag{\tag{\tag{\tag{	IBM TDB	
}		density	USPAT;	2002/05/13 11:43
_	249	silicon adj nitride with density	US-PGPUB;	
			EPO; JPO;	;
			DERWENT;	
			IBM_TDB USPAT;	2002/05/13 11:44
		1 (silicon adj nitride with density) and		
-		inter adj layer and floating with gast	EPO; JPO	
		(257/\$).ccls.	DERWENT;	
			IBM_TDB	1
		(silicon adj nitride with density) and	d USPĀT;	2002/05/13 11:49
-	3	floating with gate and (257/\$).ccls.		
		TIUGUING WICH Sand	EPO; JPC DERWENT;	
			IBM TDB	Ì
			USPAT;	2002/05/13 12:1
_	1	silicon adj nitride adj density	US-PGPUE	
	1		EPO; JPO);
			DERWENT	;
	ŧ	1	IBM TDB	

2002/05/13 12:12
2002/05/13 12:13
2002/05/13 12:14
2002, 00, ==
2002/05/13 12:14
2002/05/13 16:41
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